Product data sheet

1. General description

Hyperfast power diode in a SOD59 (2-lead TO-220AC) plastic package.

2. Features and benefits

- Fast switching
- Low leakage current
- · Low reverse recovery current
- Low thermal resistance
- · Reduces switching losses in associated MOSFET or IGBT

3. Applications

- Active PFC in air conditioner
- · High frequency switched-mode power supplies
- Continuous Current Mode (CCM) Power Factor Correction (PFC)

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Va	lues		Unit
Absolute	maximum rating						
V_{RRM}	repetitive peak reverse voltage			6	00		V
I _{F(AV)}	average forward current	δ = 0.5; T _{mb} ≤ 104 °C; square-wave pulse Fig. 1; Fig. 2; Fig. 3		30			А
I _{FRM}	repetitive peak forward current	δ = 0.5; t _p = 25 μs; T _{mb} ≤ 104 °C; square-wave pulse	60			А	
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	200 220			Α	
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse				Α	
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static ch	aracteristics			,			
V _F	forward voltage	I _F = 30 A; T _j = 150 °C; <u>Fig. 6</u>		-	1.38	1.8	V
Dynamic	characteristics				,		
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 50 \text{ A}/\mu\text{s}$; $T_j = 25 \text{ °C}$; Fig. 7		-	-	35	ns

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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode	mb	
2	А	anode	7 0 5	K -
mb	mb	mounting base; connected to cathode	1 2 TO-220AC (SOD59)	001aaa020

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BYC30-600P	TO-220AC	plastic single-ended package; heatsink mounted; 1 mounting hole; 2-lead TO-220AC	SOD59

7. Marking

Table 4. Marking codes

Type number	Marking codes
BYC30-600P	BYC30-600P

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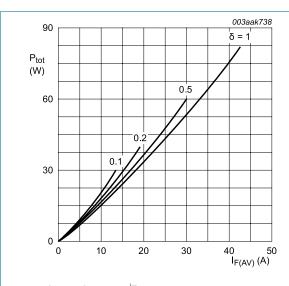
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
V_{RRM}	repetitive peak reverse voltage		600	V
V_{RWM}	crest working reverse voltage		600	V
V_R	reverse voltage	DC	600	V
$I_{F(AV)}$	average forward current	$δ$ = 0.5; T_{mb} ≤ 104 °C; square-wave pulse; Fig. 1; Fig. 2; Fig. 3	30	Α
I _{FRM}	repetitive peak forward current	δ = 0.5; t _p = 25 μs; T _{mb} ≤ 104 °C; square-wave pulse	60	Α
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	200	А
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	220	Α
T _{stg}	storage temperature		-65 to 175	°C
T _j	junction temperature		175	°C

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$$\begin{split} I_{\text{F(AV)}} &= I_{\text{F(RMS)}} \times \sqrt{\delta} \\ V_{\text{o}} &= 1.798 \text{ V; } R_{\text{s}} = 0.003 \text{ } \Omega \end{split}$$

Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values

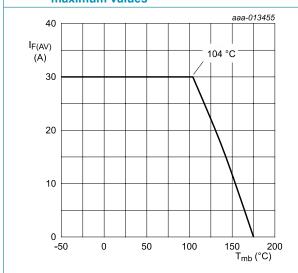
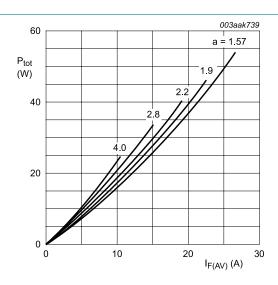


Fig. 3. Forward current as a function of mounting base temperature; maximum values



a = form factor = $I_{F(RMS)}/I_{F(AV)}$ V_o = 1.798 V; R_s = 0.003 Ω

Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

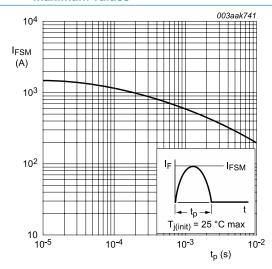


Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values

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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	with heatsink compound; Fig. 5	-	-	1.2	K/W
$R_{\text{th(j-a)}}$	thermal resistance from junction to ambient	in free air	-	60	-	K/W

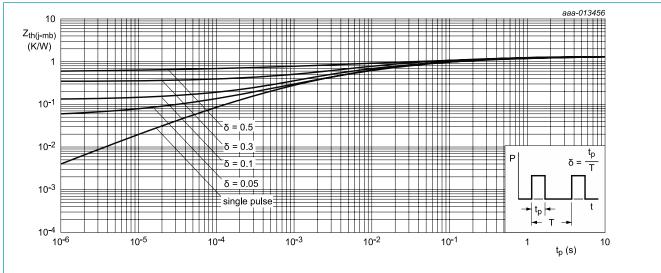
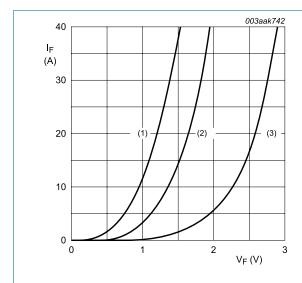


Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	M	in Ty	/p M	lax	Unit
Static cha	racteristics						
V_{F}	forward voltage	I _F = 30A; T _j = 25 °C; <u>Fig. 6</u>	-	2	2	.75	V
		I _F = 30 A; T _j = 150 °C; <u>Fig. 6</u>	-	1.	38 1	.8	٧
I _R	reverse current	V _R = 600 V; T _j = 25 °C	-	-	10	0	μΑ
		V _R = 600 V; T _j = 150 °C	-	-	1		mA
Dynamic (characteristics		'	,	,		
Q _r	recovered charge	$I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ μ s; $T_J = 25 \text{ °C}; Fig. 7$	-	50) -		nC
		$I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ μ s; $T_J = 125 ^{\circ}\text{C}; Fig. 7$	-	28	30 -		nC
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 50 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	-	3	5	ns
		$I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A/µs};$ $T_j = 25 ^{\circ}\text{C}; Fig. 7$	-	-	3	5	ns
		$I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$	-	70) -		ns
I _{RM}	peak reverse recovery current	$I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 25 ^{\circ}\text{C}; Fig. 7$	-	3.	5 -		Α
		$I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_i = 125 \text{ °C}; Fig. 7$	-	7.	6 -		Α



(1) T_j = 150 °C; typical values

(2) $T_j = 150$ °C; maximum values

(3) $T_j = 25$ °C; maximum values

 $V_0 = 1.798 \text{ V}; R_s = 0.003 \Omega$



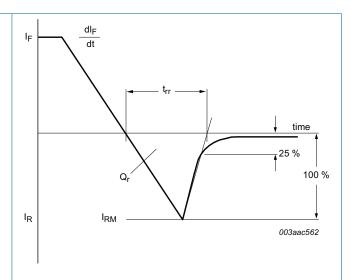
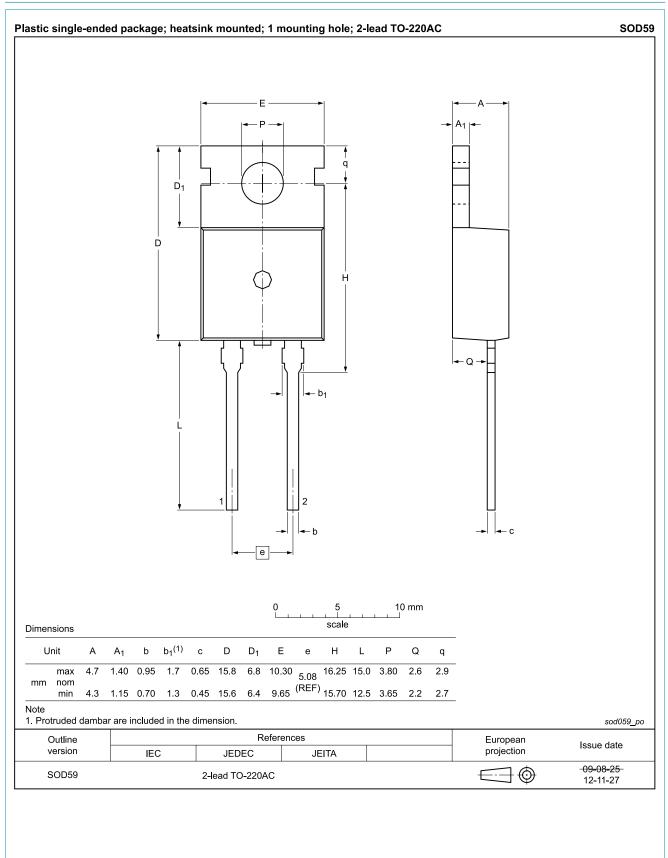


Fig. 7. Reverse recovery definitions; ramp recovery

11. Package outline



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12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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